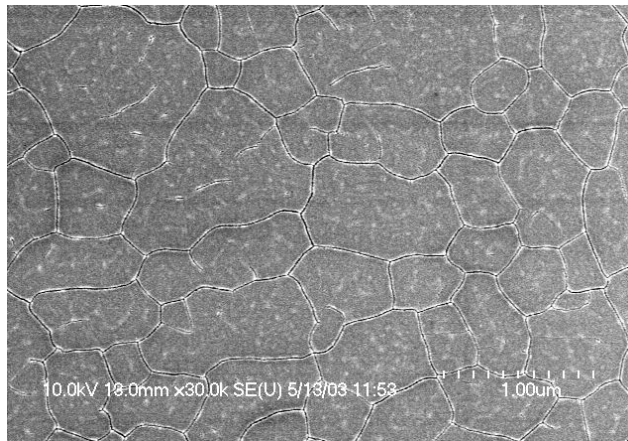
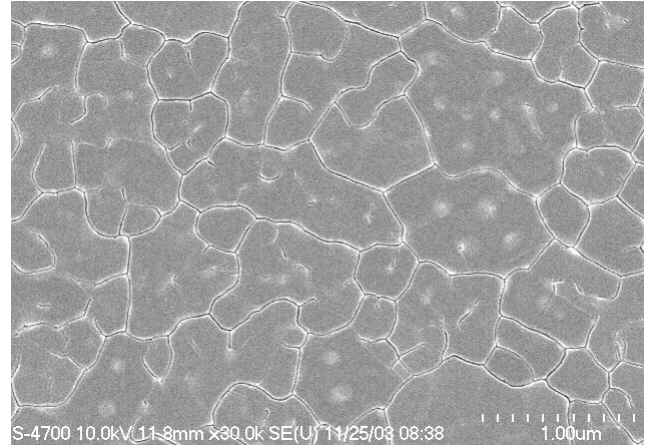


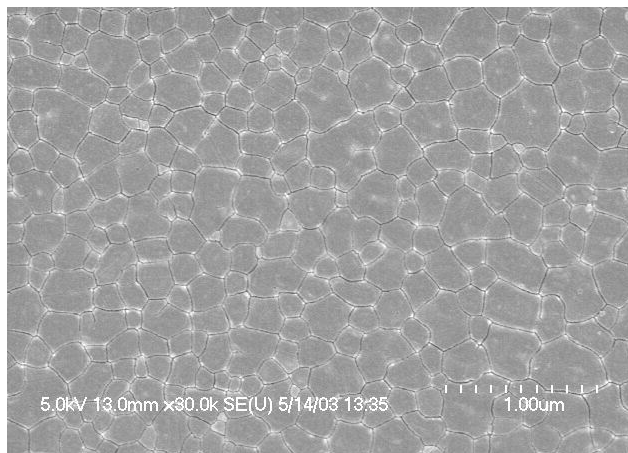
Fig. 3-22 SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 350, (b) 360, (c) 370, (d) 380 (e) 390 (f) 400 mJ/cm^2 in the O_2 ambience with concentration 100ppm. The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with HF 1% for 30sec



(a)



(b)



(c)

Fig. 3-23 SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 410, (b) 420, (c) 430 mJ/cm^2 in the O_2 ambience with concentration 100ppm. The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with HF 1% for 30sec.